NEC

MOS FIELD EFFECT TRANSISTOR
2SK4035

SWITCHING
N-CHANNEL POWER MOSFET

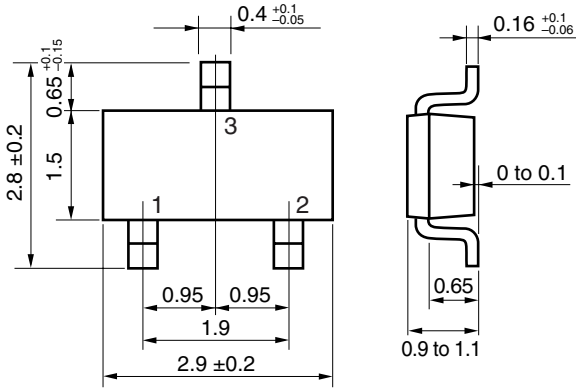
DESCRIPTION

2SK4035 is the best switching element for the DC-DC converter usage from 24 to 48 V in the direct current input voltage. It excels in the switching characteristics in low on-state resistance and because it is the small size surface mounting externals, is the best for the high-speed switching usage of the equipment that promotes the automation of space-saving and mounting.

FEATURES

- Low input capacitance
  C_{iss} = 74 pF TYP.
- Low on-state resistance
  $R_{DS(on)}$ = 4.5 Ω MAX. (V_{GS} = 10 V, I_D = 0.25 A)
- Small and surface mount package (SC-96)

PACKAGE DRAWING (Unit: mm)



1. Gate
2. Source
3. Drain

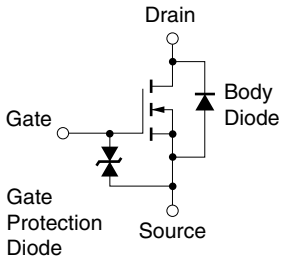
ORDERING INFORMATION

PART NUMBER	PACKAGE
2SK4035	SC-96 (Mini Mold Thin Type)
2SK4035-A **Note**	SC-96 (Mini Mold Thin Type)

Note Pb-free (This product does not contain Pb in external electrode and other parts.)

Marking: XP

EQUIVALENT CIRCUIT



ABSOLUTE MAXIMUM RATINGS (T_A = 25°C)

Drain to Source Voltage (V_{GS} = 0 V)	V_{DSS}	250	V
Gate to Source Voltage (V_{DS} = 0 V)	V_{GSS}	±30	V
Drain Current (DC) (T_A = 25°C)	$I_{D(DC)}$	±0.5	A
Drain Current (pulse) **Note1**	$I_{D(pulse)}$	±2.0	A
Total Power Dissipation (T_A = 25°C)	P_{T1}	0.2	W
Total Power Dissipation (T_A = 25°C) **Note2**	P_{T2}	1.25	W
Channel Temperature	T_{ch}	150	°C
Storage Temperature	T_{stg}	−55 to +150	°C

Notes 1. PW ≤ 10 μs, Duty Cycle ≤ 1%

2. Mounted on FR-4 board of 50 mm x 50 mm x 1.6 mm, t ≤ 5 sec

Remark The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

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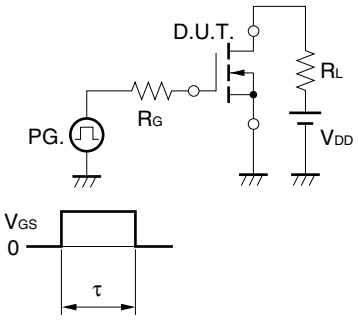
ELECTRICAL CHARACTERISTICS (T_A = 25°C)

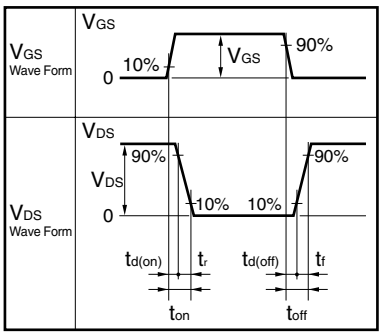
CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 250 V, V_{GS} = 0 V			10	μA
Gate Leakage Current	I_{GSS}	V_{GS} = ±30 V, V_{DS} = 0 V			±10	μA
Gate Cut-off Voltage	$V_{GS(off)}$	V_{DS} = 10 V, I_D = 1.0 mA	2.5	3.5	4.5	V
Forward Transfer Admittance **Note**	$\|y_{fs}\|$	V_{DS} = 10 V, I_D = 0.25 A	0.2	0.5		S
Drain to Source On-state Resistance **Note**	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 0.25 A		3.2	4.5	Ω
Input Capacitance	C_{iss}	V_{DS} = 10 V		74		pF
Output Capacitance	C_{oss}	V_{GS} = 0 V		16		pF
Reverse Transfer Capacitance	C_{rss}	f = 1.0 MHz		7		pF
Turn-on Delay Time	$t_{d(on)}$	V_{DD} = 125 V, I_D = 0.25 A		7		ns
Rise Time	t_r	V_{GS} = 10 V		5		ns
Turn-off Delay Time	$t_{d(off)}$	R_G = 10 Ω		12		ns
Fall Time	t_f			40		ns
Total Gate Charge	Q_G	V_{DD} = 200 V		4		nC
Gate to Source Charge	Q_{GS}	V_{GS} = 10 V		0.9		nC
Gate to Drain Charge	Q_{GD}	I_D = 0.5 A		2		nC
Body Diode Forward Voltage **Note**	$V_{F(S-D)}$	I_F = 0.5 A, V_{GS} = 0 V		0.84		V
Reverse Recovery Time	t_{rr}	I_F = 0.5 A, V_{GS} = 0 V		42		ns
Reverse Recovery Charge	Q_{rr}	di/dt = 100 A/μs		57		nC

Note Pulsed

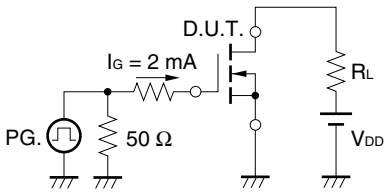
TEST CIRCUIT 1 SWITCHING TIME



τ = 1 μs
Duty Cycle ≤ 1%

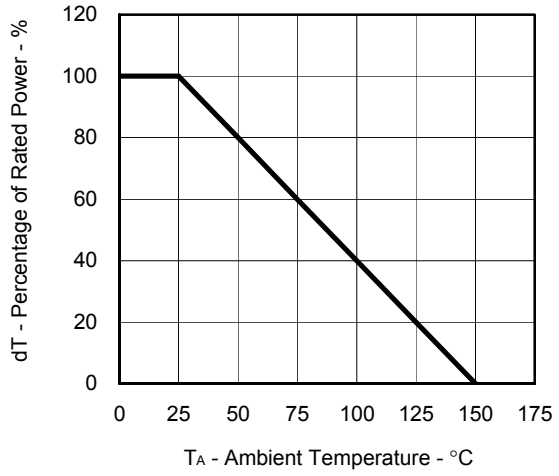


TEST CIRCUIT 2 GATE CHARGE

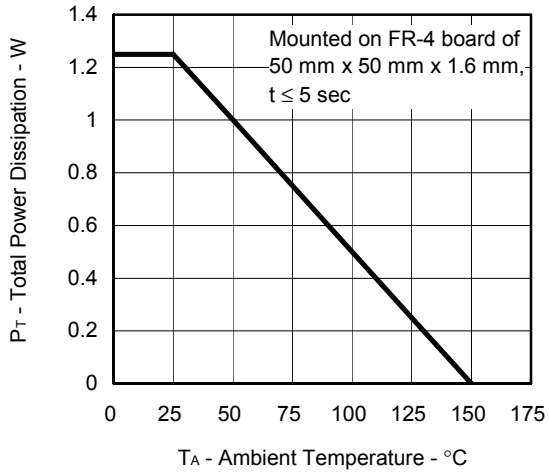


TYPICAL CHARACTERISTICS (T_A = 25°C)

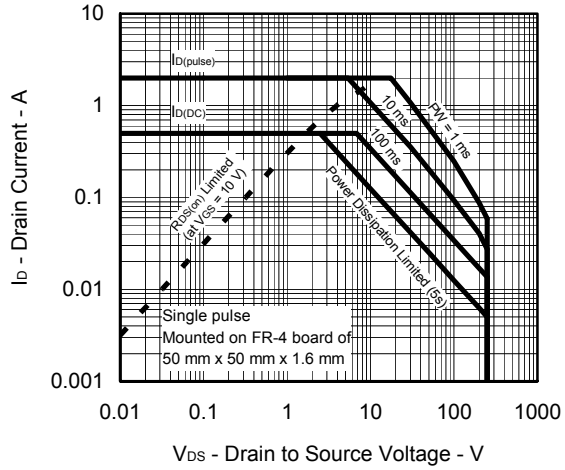
DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA



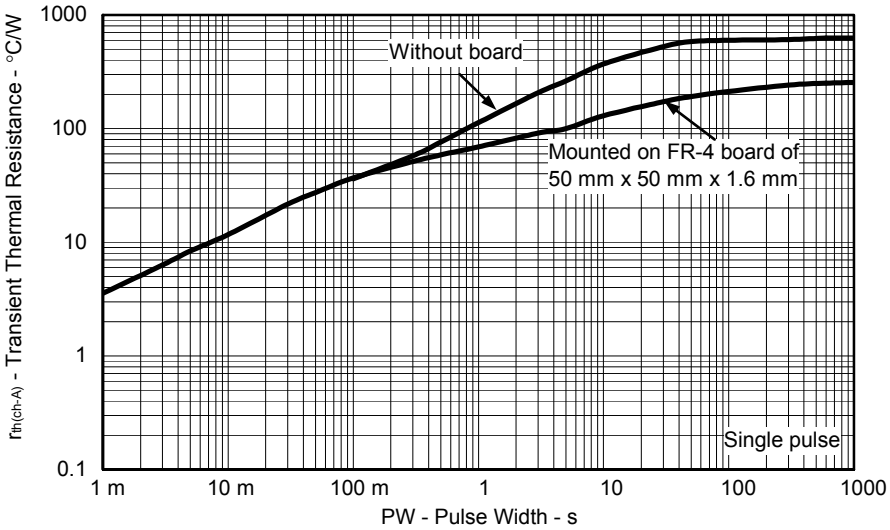
TOTAL POWER DISSIPATION vs. AMBIENT TEMPERATURE



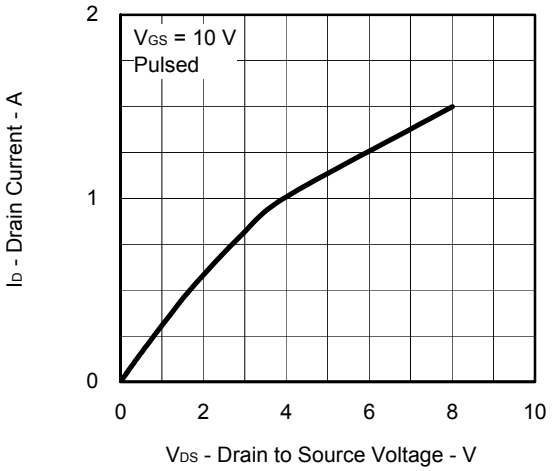
FORWARD BIAS SAFE OPERATING AREA



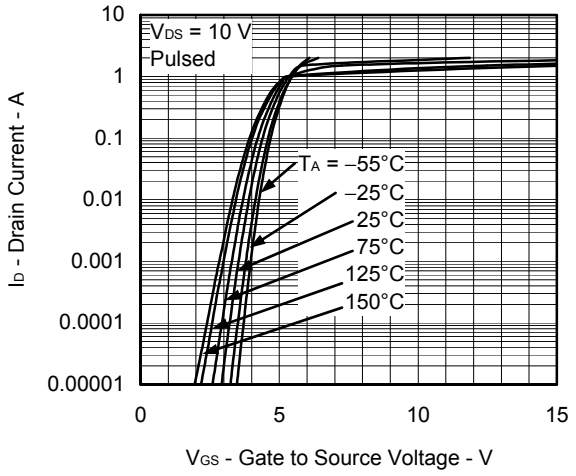
TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



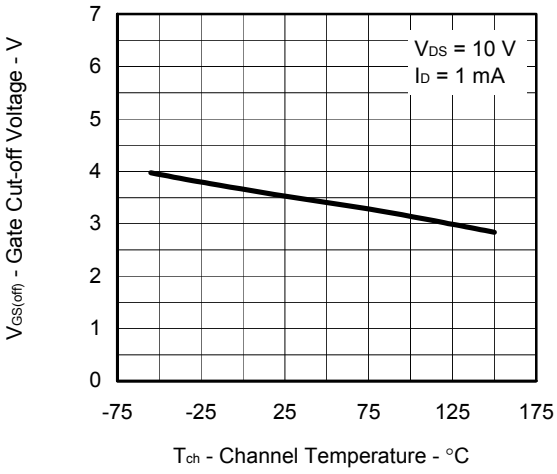
DRAIN CURRENT vs.
DRAIN TO SOURCE VOLTAGE



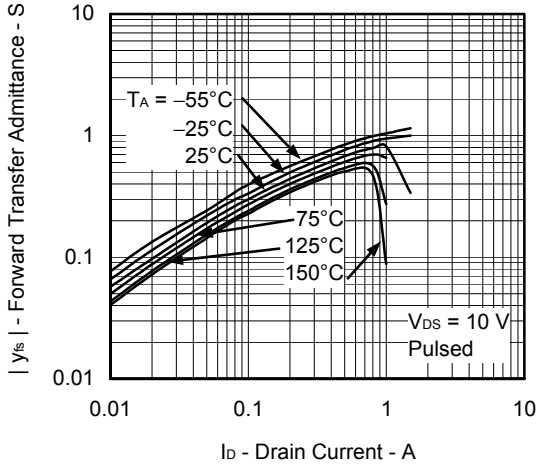
FORWARD TRANSFER CHARACTERISTICS



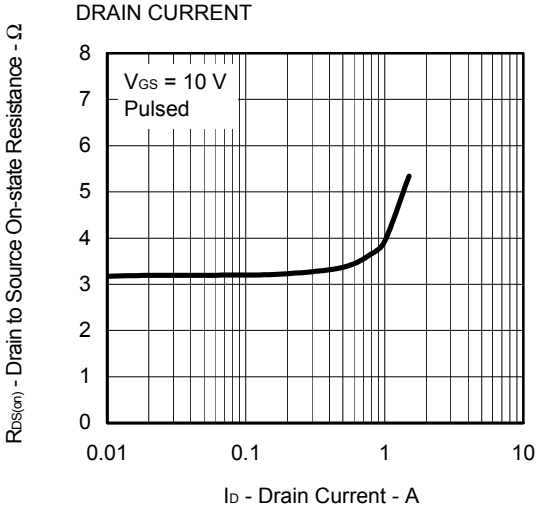
GATE CUT-OFF VOLTAGE vs.
CHANNEL TEMPERATURE



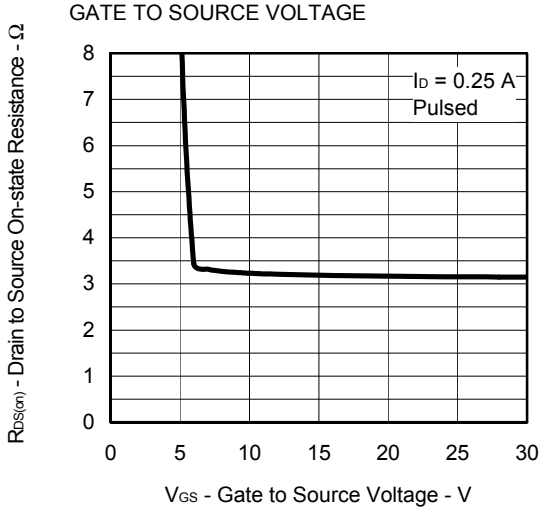
FORWARD TRANSFER ADMITTANCE vs.
DRAIN CURRENT



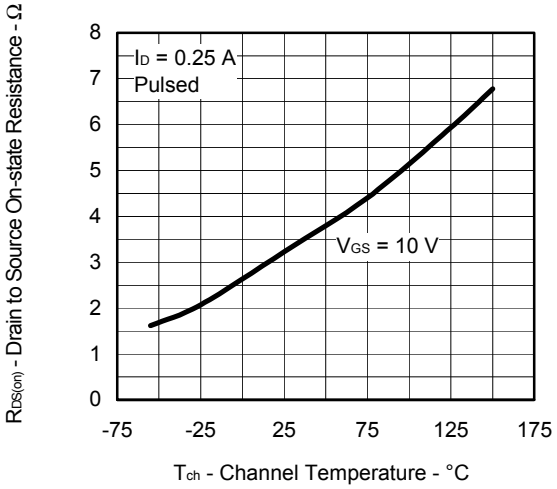
DRAIN TO SOURCE ON-STATE RESISTANCE vs.
DRAIN CURRENT



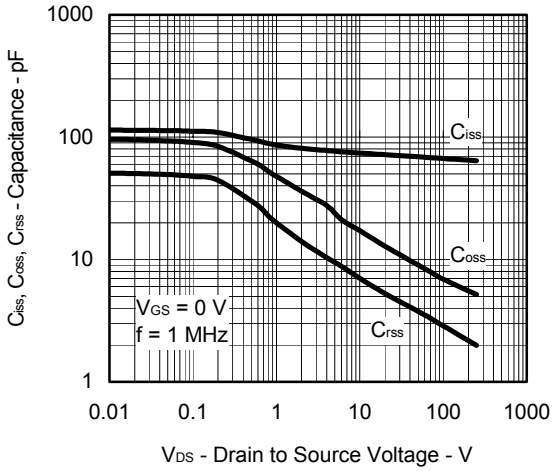
DRAIN TO SOURCE ON-STATE RESISTANCE vs.
GATE TO SOURCE VOLTAGE



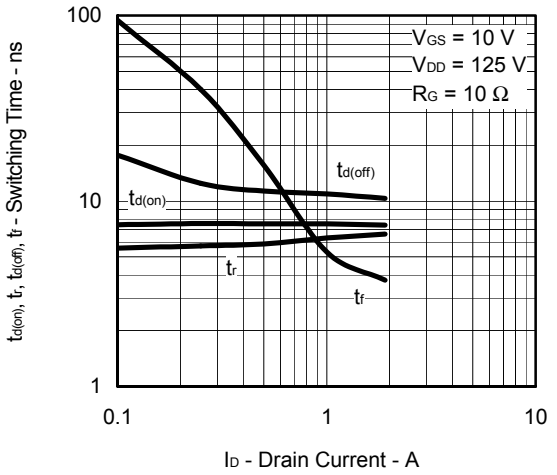
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



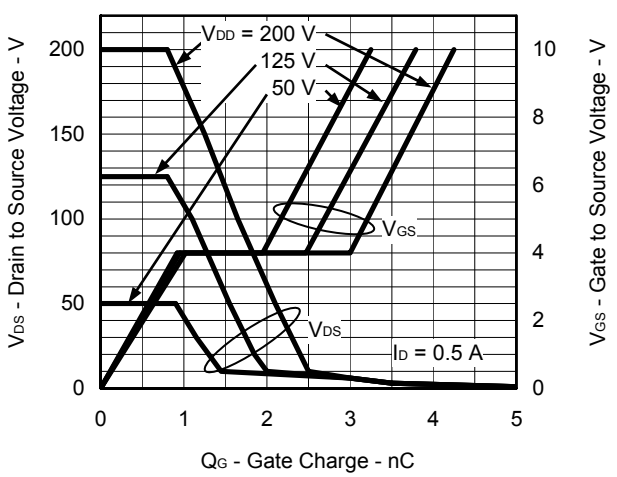
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



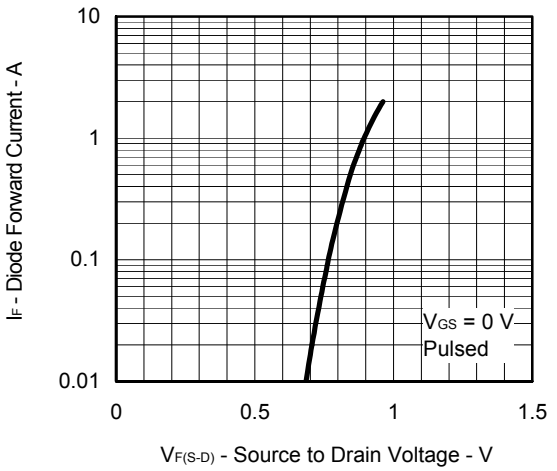
SWITCHING CHARACTERISTICS



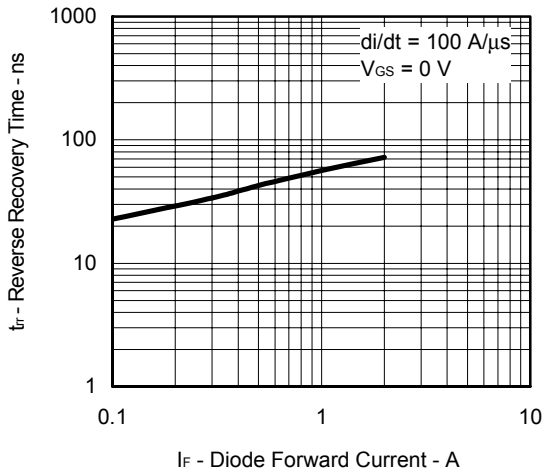
DYNAMIC INPUT/OUTPUT CHARACTERISTICS



SOURCE TO DRAIN DIODE FORWARD VOLTAGE



REVERSE RECOVERY TIME vs. DIODE FORWARD CURRENT



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